a ridge portion formed in a region having a predetermined width on said first nitride based semiconductor layer, having an upper surface having a first width and a side surface, and containing at least one of indium, gallium, aluminum, boron and thallium;

A1 cont'd

a current blocking layer formed on said first nitride based semiconductor layer and on a region from the side surface of said ridge portion to the upper surface thereof, and having an opening having a second width smaller than said first width on the upper surface of said ridge portion; and

a second nitride based semiconductor layer formed on said ridge portion inside said opening and containing at least one of indium, gallium, aluminum, boron and thallium.

11. (Amended) A method of fabricating a semiconductor laser device, comprising the steps of:

forming a first nitride based semiconductor layer including a light emitting layer and containing at least one of indium, gallium, aluminum, boron and thallium;

forming a ridge portion having an upper surface having a first width and a side surface, and

A2

containing at least one of indium, gallium, aluminum, boron and thallium in a region having a predetermined width on said first nitride based semiconductor layer;

forming on a region from the side surface of said ridge portion to the upper surface thereof a current blocking layer having an opening having a second width smaller than said first width on the upper surface of said ridge portion; and

forming a second nitride based semiconductor layer containing at least one of indium, gallium, aluminum, boron and thallium on said ridge portion inside said opening.